







SLOS377A - SEPTEMBER 2001- REVISED JULY 2003

FAMILY OF MICROPOWER RAIL-TO-RAIL INPUT AND OUTPUT OPERATIONAL AMPLIFIERS

FEATURES

- BiMOS Rail-to-Rail Input/Output
- Input Bias Current . . . 1 pA
- High Wide Bandwidth . . . 160 kHz
- High Slew Rate . . . 0.1 V/μs
- Supply Current . . . 7 μA (per channel)
- Input Noise Voltage . . . 90 nV/√Hz
- Supply Voltage Range . . . 2.7 V to 16 V
- Specified Temperature Range
 - -40°C to 125°C . . . Industrial Grade
- Ultra-Small Packaging
 - 5 Pin SOT-23 (TLV2381)

APPLICATIONS

- Portable Medical
- Power Monitoring
- Low Power Security Detection Systems
- Smoke Detectors

DESCRIPTION

The TLV238x single supply operational amplifiers provide rail-to-rail input and output capability. The TLV238x takes the minimum operating supply voltage down to 2.7 V over the extended industrial temperature range, while adding the rail-to-rail output swing feature. The TLV238x also provides 160-kHz bandwidth from only 7 μ A. The maximum recommended supply voltage is 16 V, which allows the devices to be operated from (±8 V supplies down to ±1.35 V) two rechargeable cells.

The combination of rail-to-rail inputs and outputs make them good upgrades for the TLC27Lx family—offering more bandwidth at a lower quiescent current. The offset voltage is lower than the TLC27LxA variant.

To maintain cost effectiveness the TLV2381/2 are only available in the extended industrial temperature range. This means that one device can be used in a wide range of applications that include PDAs as well as automotive sensor interface.

All members are available in SOIC, with the singles in the small SOT-23 package, duals in the MSOP.

SELECTION GUIDE

| DEVICE | V _S [V] | lQ/ch [μΑ] | VICR [V] | V _{IO} [mV] | I _{IB} [pA] | GBW [MHz] | SLEW RATE [V/μs] | V _n , 1 <u>kH</u> z [nV/√Hz] | |
|---------|-----------------------|---------------|------------------------------|-------------------------|-------------------------|--------------|---------------------|--|--|
| TLV238x | 2.7 to 16 | 10 | -0.2 to $V_{S} + 0.2$ | 4.5 | 60 | 0.16 | 0.06 | 100 | |
| TLV27Lx | 2.7 to 16 | 11 | -0.2 to V _S − 1.2 | 5 | 60 | 0.16 | 0.06 | 100 | |
| TLC27Lx | 4 to 16 | 17 | -0.2 to V _S − 1.5 | 10/5/2 | 60 | 0.085 | 0.03 | 68 | |
| OPAx349 | 1.8 to 5.5 | 2 | -0.2 to V _S + 0.2 | 10 | 10 | 0.070 | 0.02 | 300 | |
| OPAx347 | 2.3 to 5.5 | 34 | -0.2 to V _S + 0.2 | 6 | 10 | 0.35 | 0.01 | 60 | |
| TLC225x | 2.7 to 16 | 62.5 | 0 to V _S – 1.5 | 1.5/0.85 | 60 | 0.200 | 0.02 | 19 | |

NOTE: All dc specs are maximums while ac specs are typicals.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.



PACKAGE/ORDERING INFORMATION

| PRODUCT | PACKAGE | PACKAGE CODE | SYMBOL | SPECIFIED TEMPERATURE RANGE | ORDER NUMBER | TRANSPORT MEDIA | |
|-------------|---------|-----------------|--------|-----------------------------------|--------------|-----------------|--|
| TLV2381ID | SOIC-8 | D | 23811 | | TLV2381ID | Tube | |
| TLV230TID | 3010-6 | D | 23011 | | TLV2381IDR | Tape and Reel | |
| TLV2381IDBV | SOT-23 | DBV | VBKI | –40°C to 125°C | TLV2381IDBVR | Tape and Reel | |
| TLV230TIDBV | 301-23 | DBV | VDNI | -40 C to 125 C | TLV2381IDBVT | rape and Reer | |
| TLV2382ID | SOIC-8 | D | 23821 | | TLV2382ID | Tube | |
| 1 LV 23021D | 3010-6 | D | 23021 | | TLV2382IDR | Tape and Reel | |

absolute maximum ratings over operating free-air temperature (unless otherwise noted)†

| Supply voltage, V _S | 16.5 V |
|---|--------------------------------|
| Input voltage, V _I (see Notes 1 and 2) | |
| Output current, I _O | 100 mA |
| Differential input voltage, V _{ID} | V _S |
| Continuous total power dissipation | . See Dissipation Rating Table |
| Maximum junction temperature, T _J | 150°C |
| Operating free-air temperature range, T _A : I suffix | –40°C to 125°C |
| Storage temperature range, T _{stq} | |
| Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds | 300°C |

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. Relative to GND pin.

2. Maximum is 16.5 V or V_S+0.2 V whichever is the lesser value.

DISSIPATION RATING TABLE

| PACKAGE | (_o C/M) θ ¹ C | θJA (°C/W) | $T_{\mbox{\scriptsize A}} \le 25^{\circ}\mbox{\scriptsize C}$ POWER RATING | T _A = 85°C POWER RATING |
|---------|---|---------------|--|---------------------------------------|
| D (8) | D (8) 38.3 | | 710 mW | 370 mW |
| DBV (5) | 55 | 324.1 | 385 mW | 201 mW |
| DBV (6) | 55 | 294.3 | 425 mW | 221 mW |



recommended operating conditions

| | | MIN | MAX | UNIT | |
|------------------------------------|---------------|-------|---------------------|------|--|
| Supply voltage (Ve) | Dual supply | ±1.35 | ±8 | | |
| Supply voltage, (V _S) | Single supply | 2.7 | 16 | V | |
| Input common-mode voltage range | | -0.2 | V _S +0.2 | V | |
| Operating free air temperature, TA | I-suffix | -40 | 125 | °C | |

electrical characteristics at recommended operating conditions, V_S = 2.7 V, 5 V, and 15 V (unless otherwise noted)

dc performance

| | PARAMETER | TEST CONDIT | IONS | T _A † | MIN | TYP | MAX | UNIT |
|----------|-----------------------------------|---|--|------------------|-----|-----|------|-------|
| \/10 | Input offset voltage | V V (0 V |) / /O | 25°C | | 0.5 | 4.5 | mV |
| VIO | input onset voltage | $V_{IC} = V_{S}/2,$ $V_{O} = V_{S}/2$ $R_{I} = 100 \text{ k}\Omega$ $R_{S} = 50 \Omega$ | Full range | | | 6.5 | IIIV | |
| ανιο | Offset voltage drift | 1.5- | | 25°C | | 1.1 | | μV/°C |
| | | $V_{IC} = 0 V \text{ to } V_S$ | | 25°C | 54 | 69 | | |
| | | $R_S = 50 \Omega$ | V _S = 2.7 V | Full range | 53 | | | dB |
| | | $V_{IC} = 0 \text{ V to V}_{S}-1.3 \text{ V},$ | 1 3 - 2.7 | 25°C | 71 | 86 | | uВ |
| | | $R_S = 50 \Omega$ | | Full range | 70 | | | |
| | | $V_{IC} = 0 V \text{ to } V_{S},$ | | 25°C | 58 | 74 | | |
| CMRR | Common-mode rejection ratio | $R_S = 50 \Omega$ | $S = 50 \Omega$ C = 0 V to V _S -1.3 V, | Full range | 57 | | | dB |
| Civilata | Common-mode rejection ratio | $V_{IC} = 0 \text{ V to V}_{S}-1.3 \text{ V},$ $R_{S} = 50 \Omega$ | | 25°C | 72 | 88 | | |
| | | | | Full range | 70 | | | |
| | | $V_{IC} = 0 V \text{ to } V_S$ | | 25°C | 65 | 80 | | |
| | | $R_S = 50 \Omega$ | = 50 Ω V _S = 15 V | Full range | 64 | | | dB |
| | | $V_{IC} = 0 \text{ V to V}_{S}-1.3 \text{ V},$ | 7 5 - 15 4 | 25°C | 72 | 90 | | |
| | | $R_S = 50 \Omega$ | | Full range | 70 | | | |
| | | | V _S = 2.7 V | 25°C | 80 | 100 | | |
| | | | VS = 2.7 V | Full range | 77 | | | |
| ۸ | Large-signal differential voltage | $V_{O(PP)=V_{S}/2,}$ $R_{L} = 100 \text{ k}\Omega$ | V _S = 5 V | 25°C | 80 | 100 | | dB |
| AVD | amplification | | | Full range | 77 | | | uБ |
| | | | V _S = 15 V | 25°C | 77 | 83 | | |
| | | | vS = 15 v | Full range | 74 | | | |

[†] Full range is –40°C to 125°C.

input characteristics

| | PARAMETER | TEST (| CONDITIONS | TA | MIN | TYP | MAX | UNIT |
|-------------------|-------------------------------|---|--------------------------------------|--------|-----|------|------|------|
| | | | | ≤25°C | | 1 | 60 | |
| lιO | Input offset current | | | ≤70°C | | | 100 | pA |
| | | $V_{IC} = V_S/2$, | $V_O = V_S/2$, | ≤125°C | | | 1000 | |
| | | $V_{IC} = V_S/2$, $R_L = 100 \text{ k}\Omega$, | $V_O = V_S/2$, $R_S = 50 \Omega$ | ≤25°C | | 1 | 60 | |
| I _{IB} | Input bias current | | | ≤70°C | | | 200 | pA |
| | | | | ≤125°C | | | 1000 | |
| r _{i(d)} | Differential input resistance | | | 25°C | | 1000 | | GΩ |
| CIC | Common-mode input capacitance | f = 1 kHz | _ | 25°C | | 8 | · | рF |



electrical characteristics at recommended operating conditions, V_S = 2.7 V, 5 V, and 15 V (unless otherwise noted) (continued)

power supply

| | PARAMETER | TEST CONDITIONS | T _A † | MIN | TYP | MAX | UNIT |
|------|---|---|------------------|-----|-----|-----|------|
| 1 | Supply ourrent (per channel) | Vo - Vo/2 | 25°C | | 7 | 10 | ^ |
| 'DD | Supply current (per channel) | $V_O = V_S/2$ | Full range | | | 15 | μΑ |
| PSRR | Power supply rejection ratio (AVa/AVa) | V _S = 2.7 V to 16V, No load, | 25°C | 74 | 82 | | dB |
| FORK | Power supply rejection ratio (ΔVS/ΔVIO) | V _{IC} = V _S /2 V | Full range | 70 | | | uБ |

[†] Full range is –40°C to 125°C for I suffix.

output characteristics

| | PARAMETER | TEST CONDI | TIONS | T _A † | MIN | TYP | MAX | UNIT |
|-----------------|--------------------------------|---|------------------------|------------------|-----|-----|-----|------|
| | | | V _S = 2.7 V | 25°C | 200 | 160 | | |
| | | V10 - V0/2 | VS - 2.7 V Fu | Full range | 220 | | | |
| | | | V- 5.V | 25°C | 120 | 85 | | mV |
| | | I _O = 100 μA | V _S = 5 V | Full range | 200 | | | IIIV |
| \/ ₀ | Output voltage swing from rail | V2 45 V | 25°C | 120 | 50 | | | |
| ۷o | Output voltage swing from fail | | V _S = 15 V | Full range | 150 | | | |
| | | | V _S = 5 V | 25°C | 800 | 420 | | |
| | | $V_{IC} = V_S/2$, | VS = 5 V | Full range | 900 | | | mV |
| | | V _{IC} = V _S /2, I _O = 500 μA | Vs = 15 V | 25°C | 400 | 200 | | IIIV |
| | | | VS = 15 V | Full range | 500 | | | |
| I _O | Output current | $V_O = 0.5 \text{ V from rail}$ | V _S = 2.7 V | 25°C | | 400 | | μΑ |

[†] Full range is –40°C to 125°C for I suffix.

dynamic performance

|) | | | | | |
|----------------|-------------------------|---|-------|-------------|------|
| | PARAMETER | TEST CONDITIONS | TA | MIN TYP MAX | UNIT |
| GBP | Gain bandwidth product | $R_L = 100 \text{ k}\Omega$, $C_L = 10 \text{ pF}$, $f = 1 \text{ kHz}$ | 25°C | 160 | kHz |
| | | | 25°C | 0.06 | |
| SR | Slew rate at unity gain | $V_{O(pp)} = 2 \text{ V}, R_L = 100 \text{ k}\Omega,$ $C_L = 10 \text{ pF}$ | -40°C | 0.05 | V/μs |
| | | о_ = 10 рі | 125°C | 0.08 | 1 |
| φм | Phase margin | D. 400 kg C. 50 pF | 25°C | 62 | ٥ |
| | Gain margin | $R_L = 100 \text{ k}Ω$, $C_L = 50 \text{ pF}$ | 25°C | 6.7 | dB |
| | Sattling time (0.19/) | V(STEP)pp = 1 V, AV = -1, Rise | 25°C | 31 | |
| t _S | Settling time (0.1%) | $V(STEP)pp = 1 V$, $AV = -1$, Rise $C_L = 10 pF$, $R_L = 100 k\Omega$ Fall | 25 6 | 61 | μs |

noise/distortion performance

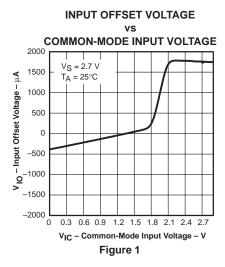
| - 1 | | • | | | | | | |
|-----|----|--------------------------------|-----------------|------|-----|-----|-----|--------|
| | | PARAMETER | TEST CONDITIONS | TA | MIN | TYP | MAX | UNIT |
| | Vn | Equivalent input noise voltage | f = 1 kHz | 25°C | | 90 | | nV/√Hz |

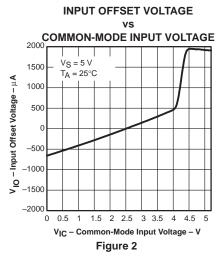


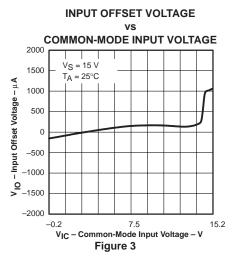
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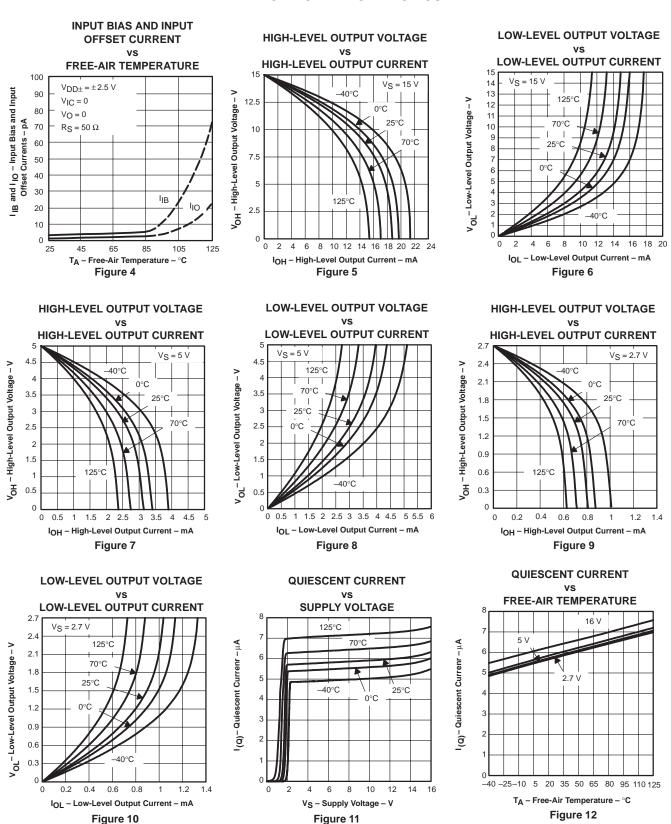
Table of Graphs

| | | | FIGURE |
|----------------------------------|---|------------------------------|----------|
| VIO | Input offset voltage | vs Common-mode input voltage | 1, 2, 3 |
| I _{IB} /I _{IO} | Input bias and offset current | vs Free-air temperature | 4 |
| Vон | High-level output voltage | vs High-level output current | 5, 7, 9 |
| VOL | Low-level output voltage | vs Low-level output current | 6, 8, 10 |
| 1- | Quiescent current | vs Supply voltage | 11 |
| IQ | Quiescent current | vs Free-air temperature | 12 |
| | Supply voltage and supply current ramp up | | 13 |
| A _{VD} | Differential voltage gain and phase shift | vs Frequency | 14 |
| GBP | Gain-bandwidth product | vs Free-air temperature | 15 |
| φm | Phase margin | vs Load capacitance | 16 |
| CMRR | Common-mode rejection ratio | vs Frequency | 17 |
| PSRR | Power supply rejection ratio | vs Frequency | 18 |
| | Input referred noise voltage | vs Frequency | 19 |
| SR | Slew rate | vs Free-air temperature | 20 |
| VO(PP) | Peak-to-peak output voltage | vs Frequency | 21 |
| <u> </u> | Inverting small-signal response | | 22 |
| | Inverting large-signal response | | 23 |
| | Crosstalk | vs Frequency | 24 |











SUPPLY VOLTAGE AND SUPPLY CURRENT RAMP UP 40 V_S - Supply Voltage - V/dc ٧s 10 ۷o $V_S = 0 \text{ to } 15 \text{ V},$ CC - Supply Current - µ A $R_L = 100 \Omega$, C_L = 10 pF, T_A = 25°C 15 5 t - Time - ms Figure 13

DIFFERENTIAL VOLTAGE GAIN AND PHASE SHIFT

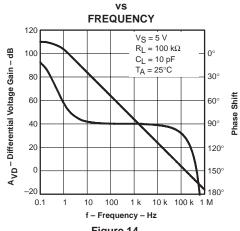
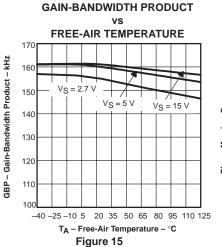
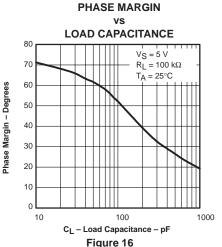
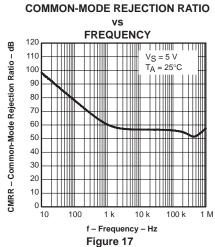


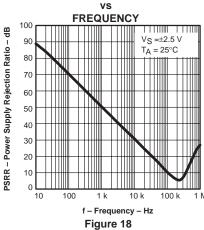
Figure 14



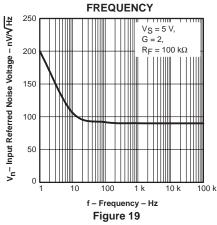


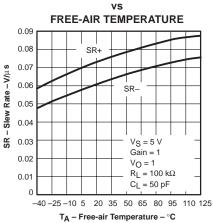


POWER SUPPLY REJECTION RATIO vs







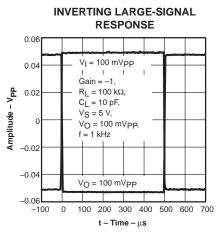


SLEW RATE

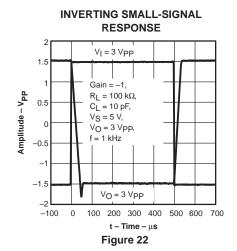
Figure 20



PEAK-TO-PEAK OUTPUT VOLTAGE vs **FREQUENCY** 16 V_{OPP} - Output Voltage Peak-to-Peak - V V_S = 15 V 12 $R_L = 100 \text{ k}\Omega$ 10 $C_{L} = 10 \text{ pF},$ THD+N <= 5% 8 V_S = 5 V $V_S = 2.7 V$ ٥١ 10 1000 100 10 k f – Frequency – Hz Figure 21







CROSSTALK vs **FREQUENCY** $V_S = 5 V$ $R_L = 2 k\Omega$ $C_L = 10 pF$ -20 $T_A = 25^{\circ}C$ -40 Channel 1 to 2 Crosstalk – dB -60 -80 -100 -120 -140 10 k 100 k 10 100 1 k f - Frequency - Hz

Figure 24



APPLICATION INFORMATION

offset voltage

The output offset voltage (V_{OO}) is the sum of the input offset voltage (V_{IO}) and both input bias currents (I_{IB}) times the corresponding gains. The following schematic and formula can be used to calculate the output offset voltage:

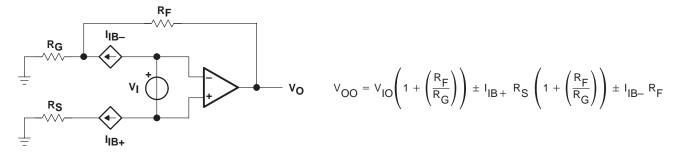


Figure 25. Output Offset Voltage Model

general configurations

When receiving low-level signals, limiting the bandwidth of the incoming signals into the system is often required. The simplest way to accomplish this is to place an RC filter at the noninverting terminal of the amplifier (see Figure 26).

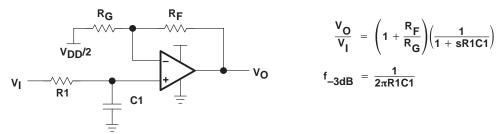


Figure 26. Single-Pole Low-Pass Filter

If even more attenuation is needed, a multiple pole filter is required. The Sallen-Key filter can be used for this task. For best results, the amplifier should have a bandwidth that is 8 to 10 times the filter frequency bandwidth. Failure to do this can result in phase shift of the amplifier.

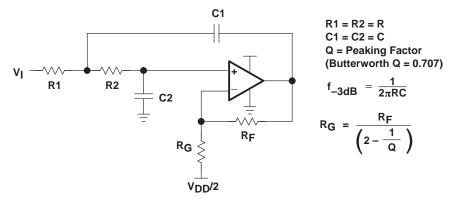


Figure 27. 2-Pole Low-Pass Sallen-Key Filter



APPLICATION INFORMATION

circuit layout considerations

To achieve the levels of high performance of the TLV238x, follow proper printed-circuit board design techniques. A general set of guidelines is given in the following.

- Ground planes—It is highly recommended that a ground plane be used on the board to provide all
 components with a low inductive ground connection. However, in the areas of the amplifier inputs and
 output, the ground plane can be removed to minimize the stray capacitance.
- Proper power supply decoupling—Use a 6.8-μF tantalum capacitor in parallel with a 0.1-μF ceramic capacitor on each supply terminal. It may be possible to share the tantalum among several amplifiers depending on the application, but a 0.1-μF ceramic capacitor should always be used on the supply terminal of every amplifier. In addition, the 0.1-μF capacitor should be placed as close as possible to the supply terminal. As this distance increases, the inductance in the connecting trace makes the capacitor less effective. The designer should strive for distances of less than 0.1 inches between the device power terminals and the ceramic capacitors.
- Sockets—Sockets can be used but are not recommended. The additional lead inductance in the socket pins
 will often lead to stability problems. Surface-mount packages soldered directly to the printed-circuit board
 is the best implementation.
- Short trace runs/compact part placements—Optimum high performance is achieved when stray series inductance has been minimized. To realize this, the circuit layout should be made as compact as possible, thereby minimizing the length of all trace runs. Particular attention should be paid to the inverting input of the amplifier. Its length should be kept as short as possible. This will help to minimize stray capacitance at the input of the amplifier.
- Surface-mount passive components—Using surface-mount passive components is recommended for high
 performance amplifier circuits for several reasons. First, because of the extremely low lead inductance of
 surface-mount components, the problem with stray series inductance is greatly reduced. Second, the small
 size of surface-mount components naturally leads to a more compact layout thereby minimizing both stray
 inductance and capacitance. If leaded components are used, it is recommended that the lead lengths be
 kept as short as possible.



APPLICATION INFORMATION

general power dissipation considerations

For a given θ_{JA} , the maximum power dissipation is shown in Figure 28 and is calculated by the following formula:

$$P_{D} = \left(\frac{T_{MAX} - T_{A}}{\theta_{JA}}\right)$$

Where:

P_D = Maximum power dissipation of TLV238x IC (watts)

 T_{MAX} = Absolute maximum junction temperature (150°C)

 T_A = Free-ambient air temperature (°C)

 $\theta_{JA} = \theta_{JC} + \theta_{CA}$

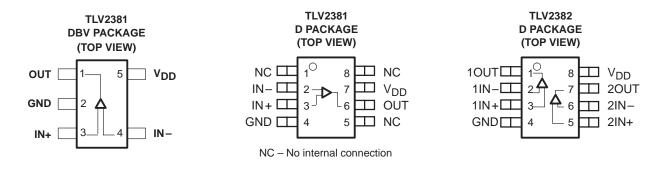
 θ_{JC} = Thermal coefficient from junction to case

 θ_{CA} = Thermal coefficient from case to ambient air (°C/W)

MAXIMUM POWER DISSIPATION FREE-AIR TEMPERATURE 2 Г」 = 150°C PDIP Package Low-K Test PCB 1.75 θ_{JA} = 104°C/W Maximum Power Dissipation - W 1.5 MSOP Package Low-K Test PCB **SOIC Package** θ_{JA} = 260°C/W 1.25 Low-K Test PCB = 176°C/W 0.75 0.5 0.25 SOT-23 Package Low-K Test PCB $\theta_{JA} = 324^{\circ}\text{C/W}$ -55-40-25-10 5 20 35 50 65 80 95 110 125 T_A - Free-Air Temperature - °C

NOTE A: Results are with no air flow and using JEDEC Standard Low-K test PCB.

Figure 28. Maximum Power Dissipation vs Free-Air Temperature





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PACKAGING INFORMATION

| Orderable Device | Status | Package Type | Package Drawing | Pins | Package Qty | Eco Plan | Lead finish/ Ball material | MSL Peak Temp | Op Temp (°C) | Device Marking (4/5) | Samples |
|------------------|--------|--------------|--------------------|------|----------------|--------------|-------------------------------|--------------------|--------------|-------------------------|---------|
| TLV2381ID | ACTIVE | SOIC | D | 8 | 75 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 125 | 23811 | Samples |
| TLV2381IDBVR | ACTIVE | SOT-23 | DBV | 5 | 3000 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 125 | VBKI | Samples |
| TLV2381IDBVRG4 | ACTIVE | SOT-23 | DBV | 5 | 3000 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 125 | VBKI | Samples |
| TLV2381IDBVT | ACTIVE | SOT-23 | DBV | 5 | 250 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 125 | VBKI | Samples |
| TLV2381IDR | ACTIVE | SOIC | D | 8 | 2500 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 125 | 23811 | Samples |
| TLV2382ID | ACTIVE | SOIC | D | 8 | 75 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 125 | 23821 | Samples |
| TLV2382IDG4 | ACTIVE | SOIC | D | 8 | 75 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 125 | 23821 | Samples |
| TLV2382IDR | ACTIVE | SOIC | D | 8 | 2500 | RoHS & Green | NIPDAU | Level-1-260C-UNLIM | -40 to 125 | 23821 | Samples |

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.



PACKAGE OPTION ADDENDUM

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(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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TAPE AND REEL INFORMATION





| A0 | |
|----|---|
| B0 | Dimension designed to accommodate the component length |
| K0 | Dimension designed to accommodate the component thickness |
| W | Overall width of the carrier tape |
| P1 | Pitch between successive cavity centers |

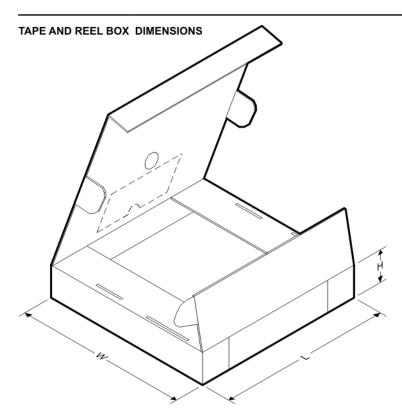
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

| All dimensions are nominal | | | | | | | | | | | | |
|----------------------------|--------|--------------------|---|------|--------------------------|--------------------------|------------|------------|------------|------------|-----------|------------------|
| Device | _ | Package Drawing | | SPQ | Reel Diameter (mm) | Reel Width W1 (mm) | A0 (mm) | B0 (mm) | K0 (mm) | P1 (mm) | W (mm) | Pin1 Quadrant |
| TLV2381IDBVR | SOT-23 | DBV | 5 | 3000 | 180.0 | 9.0 | 3.15 | 3.2 | 1.4 | 4.0 | 8.0 | Q3 |
| TLV2381IDBVT | SOT-23 | DBV | 5 | 250 | 180.0 | 9.0 | 3.15 | 3.2 | 1.4 | 4.0 | 8.0 | Q3 |
| TLV2381IDR | SOIC | D | 8 | 2500 | 330.0 | 12.4 | 6.4 | 5.2 | 2.1 | 8.0 | 12.0 | Q1 |
| TLV2382IDR | SOIC | D | 8 | 2500 | 330.0 | 12.4 | 6.4 | 5.2 | 2.1 | 8.0 | 12.0 | Q1 |

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*All dimensions are nominal

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|-------------------------------------|--------------|-----------------|------|------|-------------|------------|-------------|
| Device | Package Type | Package Drawing | Pins | SPQ | Length (mm) | Width (mm) | Height (mm) |
| TLV2381IDBVR | SOT-23 | DBV | 5 | 3000 | 182.0 | 182.0 | 20.0 |
| TLV2381IDBVT | SOT-23 | DBV | 5 | 250 | 182.0 | 182.0 | 20.0 |
| TLV2381IDR | SOIC | D | 8 | 2500 | 340.5 | 336.1 | 25.0 |
| TLV2382IDR | SOIC | D | 8 | 2500 | 340.5 | 336.1 | 25.0 |

PACKAGE MATERIALS INFORMATION

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TUBE



*All dimensions are nominal

| Device | Package Name | Package Type | Pins | SPQ | L (mm) | W (mm) | T (µm) | B (mm) |
|-------------|--------------|--------------|------|-----|--------|--------|--------|--------|
| TLV2381ID | D | SOIC | 8 | 75 | 507 | 8 | 3940 | 4.32 |
| TLV2382ID | D | SOIC | 8 | 75 | 507 | 8 | 3940 | 4.32 |
| TLV2382IDG4 | D | SOIC | 8 | 75 | 507 | 8 | 3940 | 4.32 |



SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 2. This drawing is subject to change without notice.
 3. Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE TRANSISTOR



NOTES: (continued)



^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

^{8.} Board assembly site may have different recommendations for stencil design.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

- 1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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